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updatedIN THE SPECIFICATION

Page 1, before the first line, add the paragraph:

--This is a continuation application of U.S. Serial No. 09/961,250, filed September 25, 2001, <sup>is now a U.S. Patent 6,731,167</sup>---

Page 12, after line 14, add the following paragraph:

--Fig. 23 is a circuit diagram showing the relationship between an equivalent circuit of a conventional dual band type high frequency power amplifier module incorporating a GSM and a DCS and semiconductor chips and the like.--

Page 21, the second full paragraph (lines 10-23), amend the paragraph as follows:

It is one of the features of the invention that the gate electrodes (G) and drain electrodes (D) of the first ~~FETs~~ FETs and second FETs are laid out such that they are alternately provided in the same direction. In such a layout, the direction of extracting the output of the first FETs (first amplifying stage) or the direction in which wires extend therefrom is not close and adjacent to the direction of extracting the output of the second FETs (second amplifying stage) or the direction in which wires extend therefrom (see Fig. 13), which makes it possible to present any reduction in